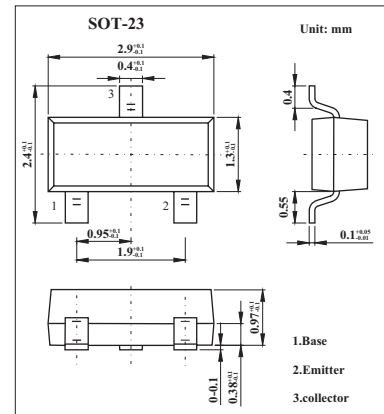


Silicon Pnp Epitaxial Planar Type

2SA1245

■ Features

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-15	V
Collector-Emitter Voltage	V_{CE0}	-8	V
Emitter-Base Voltage	V_{EB0}	-2	V
Collector Current	I_C	-30	mA
Base Current	I_B	-15	mA
Collector Power Dissipation	P_C	150	Mw
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=-5V; I_E=0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-1V; I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-5V; I_C=-10\text{mA}$	20			
Output Capacitance	C_{ob}	$V_{CB}=-5V; I_E=0; f=1\text{MHz}$		0.75		pF
Reserve Transfer Capacitance	C_{re}			0.60		pF
Transition Frequency	F_t	$V_{CE}=-5V; I_C=-10\text{mA}$		4		GHz
Insertion Gain	$ S_{21e} ^2(1)$	$V_{CE}=-5V; I_C=-10\text{mA}; f=500\text{MHz}$		14		dB
	$ S_{21e} ^2(2)$	$V_{CE}=-5V; I_C=-10\text{mA}; f=1\text{GHz}$		9.5		dB
Noise Figure	NF(1)	$V_{CE}=-5V; I_C=-3\text{mA}; f=500\text{MHz}$		2.5		dB
	NF(2)	$V_{CE}=-5V; I_C=-3\text{mA}; f=1\text{GHz}$		3.0		dB

■ Marking

Marking	MD